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Amendments to the Claims

Please amend the claims as follows:

1. (canceled): A method for forming an isolation region comprising the steps of:
 providing a region of semiconductor material;
 forming a tub in the region of semiconductor material, wherein the tub includes a plurality of shapes; and
 exposing the plurality of shapes to an ambient that includes a chemical species that reacts with the plurality shapes to form the isolation region, and wherein the plurality of shapes form part of the isolation region.
2. (canceled): The method of claim 1 wherein the step of exposing includes thermally oxidizing the plurality of shapes to form a silicon oxide isolation region.
3. (canceled): The method of claim 1 wherein the step of forming the tub includes forming the tub having a boundary around the plurality of shapes, wherein the boundary includes a recessed portion.
4. (canceled): The method of claim 1 wherein the step of exposing includes consuming substantially all of the plurality of shapes.
5. (canceled): The method of claim 1 further comprising the step of forming a passive device over the isolation region.
6. (canceled): The method of claim 1 wherein the step of forming the tub includes etching exposed portions of the region of semiconductor material, and wherein the plurality

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of shapes comprise unexposed portions of the region of semiconductor material.

7. (canceled): The method of claim 6 wherein the step of etching includes etching to a depth from about 6 microns to about 10 microns.

8. (canceled): The method of claim 1, wherein the step of forming the tub includes forming a tub having a matrix of free standing shapes, wherein adjacent rows of shapes are offset from each other.

9. (canceled): The method of claim 1 wherein the step of providing the region of semiconductor material includes providing a region comprising silicon.

10. (previously presented): A process for forming an integrated circuit device including the steps of:

forming a tub region within a semiconductor layer, wherein tub region includes a matrix of shapes comprising offset rows; and

forming a dielectric region within the matrix of shapes.

11. (previously presented): The process of claim 10 wherein the step of forming the tub region includes forming a tub region with a matrix of squares.

12. (original): The process of claim 10 wherein the step of forming the dielectric region includes oxidizing the matrix of shapes.

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13. (original): The process of claim 12 wherein the step of oxidizing forms a nearly continuous silicon oxide tub.

14. (original): The process of claim 10 further comprising the step of forming a passive component over the dielectric region.

15. (original): The process of claim 10 further comprising the step of forming an isolation trench in the region of semiconductor material.

16. (original): The process of claim 10 further comprising the steps of:

forming a dielectric layer on sidewalls of the matrix of shapes; and

forming a polycrystalline semiconductor layer over the dielectric layer.

17. (previously presented): The process of claim 10 wherein the step of forming tub region includes forming tub region having a matrix of shapes wherein shapes in a first row have a first spacing, and wherein the shapes in the first row have a second spacing from shapes in a second row, and wherein the second spacing is less than the first spacing.

18. (previously presented): A semiconductor device comprising:

a region of semiconductor material; and

a dielectric tub formed in the region of semiconductor material, wherein the dielectric tub includes a matrix of passivated shapes, and wherein adjacent rows of passivated shapes are offset.

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19. (original): The device of claim 18 wherein the dielectric tub comprises oxidized silicon shapes.

20. (original): The device of claim 18 wherein the dielectric tub includes a boundary having a recessed portion.